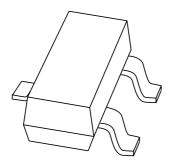
DISCRETE SEMICONDUCTORS

DATA SHEET



BAT54 seriesSchottky barrier (double) diodes

Product data sheet Supersedes data of 2001 Oct 12 2002 Mar 04



Schottky barrier (double) diodes

BAT54 series

FEATURES

- Low forward voltage
- · Guard ring protected
- · Small plastic SMD package.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- · Protection circuits
- Blocking diodes.

DESCRIPTION

Planar Schottky barrier diodes encapsulated in a SOT23 small plastic SMD package. Single diodes and double diodes with different pinning are available.

MARKING

| TYPE NUMBER | MARKING CODE(1) |
|-------------|-----------------|
| BAT54 | L4* |
| BAT54A | L42 or *V3 |
| BAT54C | L43 or *W1 |
| BAT54S | L44 or *V4 |

Note

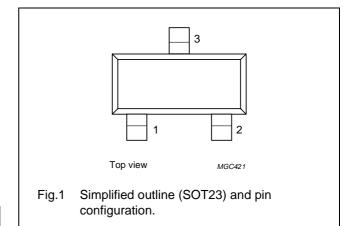
1. * = p: Made in Hong Kong.

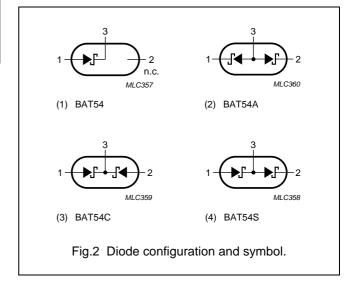
* = t : Made in Malaysia.

* = W: Made in China.

PINNING

| PIN | DESCRIPTION | | | | | | |
|-----|-------------|---------------------------------|---------------------------------|---------------------------------|--|--|--|
| FIN | BAT54 | BAT54A | BAT54C | BAT54S | | | |
| 1 | а | k ₁ | a ₁ | a ₁ | | | |
| 2 | n.c. | k ₂ | a ₂ | k ₂ | | | |
| 3 | k | a ₁ , a ₂ | k ₁ , k ₂ | k ₁ , a ₂ | | | |





Schottky barrier (double) diodes

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|--|------|------|------|
| Per diode | | · | | | |
| V _R | continuous reverse voltage | | _ | 30 | V |
| I _F | continuous forward current | | - | 200 | mA |
| I _{FRM} | repetitive peak forward current | $t_p \le 1 \text{ s; } \delta \le 0.5$ | - | 300 | mA |
| I _{FSM} | non-repetitive peak forward current | t _p < 10 ms | - | 600 | mA |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| T _j | junction temperature | | - | 125 | °C |
| Per device | | | | | |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | _ | 230 | mW |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|-------------------------------------|------------|-------|------|
| R _{th j-a} | thermal resistance from junction to | note 1 | 500 | K/W |
| 1 | ambient | | | |

Note

1. Refer to SOT23 standard mounting conditions.

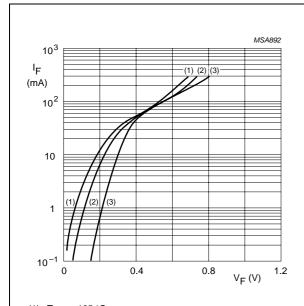
CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MAX. | UNIT |
|-----------------|-----------------------|---|------|------|
| Per diode | | | | |
| V _F | forward voltage | see Fig.3 | | |
| | | $I_F = 0.1 \text{ mA}$ | 240 | mV |
| | | I _F = 1 mA | 320 | mV |
| | | I _F = 10 mA | 400 | mV |
| | | I _F = 30 mA | 500 | mV |
| | | I _F = 100 mA | 800 | mV |
| I _R | reverse current | V _R = 25 V; see Fig.4 | 2 | μΑ |
| t _{rr} | reverse recovery time | when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.6 | 5 | ns |
| C _d | diode capacitance | $f = 1 \text{ MHz}; V_R = 1 \text{ V}; \text{ see Fig.5}$ | 10 | pF |

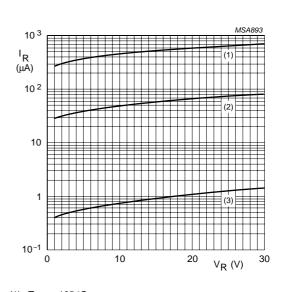
Schottky barrier (double) diodes

BAT54 series



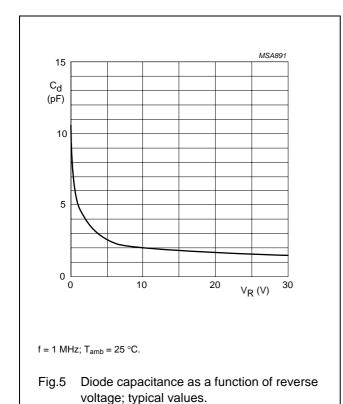
- (1) $T_{amb} = 125 \,^{\circ}C$.
- (2) $T_{amb} = 85 \,^{\circ}C$.
- (3) $T_{amb} = 25 \,^{\circ}C$.

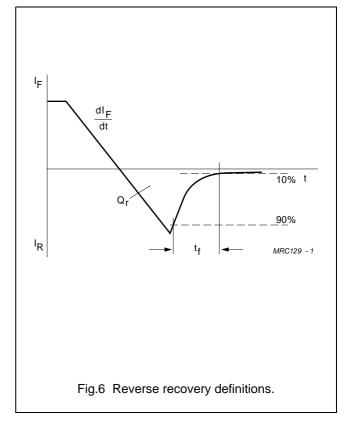
Fig.3 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \,^{\circ}C$.
- (3) $T_{amb} = 25 \,^{\circ}C$.

Fig.4 Reverse current as a function of reverse voltage; typical values.





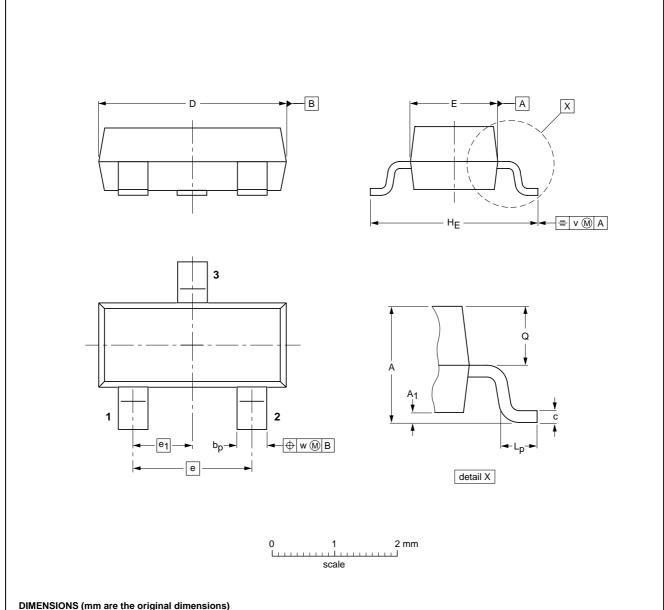
Schottky barrier (double) diodes

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



| UNIT | A | A ₁ max. | bp | С | D | E | е | e ₁ | HE | L _p | Q | ٧ | w |
|------|------------|------------------------|--------------|--------------|------------|------------|-----|----------------|------------|----------------|--------------|-----|-----|
| mm | 1.1 0.9 | 0.1 | 0.48 0.38 | 0.15 0.09 | 3.0 2.8 | 1.4 1.2 | 1.9 | 0.95 | 2.5 2.1 | 0.45 0.15 | 0.55 0.45 | 0.2 | 0.1 |

| OUTLINE | | REFER | EUROPEAN | ISSUE DATE | | |
|---------|-----|----------|----------|------------|------------|---------------------------------|
| VERSION | IEC | JEDEC | EIAJ | | PROJECTION | ISSUE DATE |
| SOT23 | | TO-236AB | | | | 97-02-28 99-09-13 |

2002 Mar 04 5

Schottky barrier (double) diodes

BAT54 series

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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